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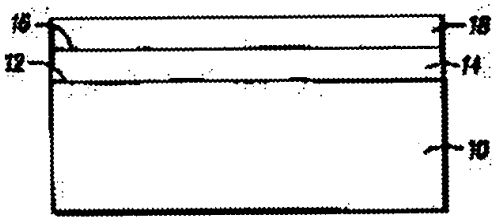
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(54) METHOD OF MANUFACTURING SEMICONDUCTOR STRUCTURE HAVING METAL OXIDE INTERFACE WITH SILICON

(57)Abstract:
PROBLEM TO BE SOLVED: To provide a method of manufacturing semiconductor structure with which a thin stable silicide interface with silicon can be manufactured.
SOLUTION: This method of manufacturing semiconductor structure comprises a step of providing a silicon substrate 10 having a surface 12, a step of forming seed layers 20 and 20' composed of silicide materials on the surface 12 of the substrate 10 by atomic layer deposition(ALD), and a step of forming one or more layers of an oxide 40 having a high dielectric constant on the seed layers 20 and 20' by atomic layer deposition(ALD).



LEGAL STATUS

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